

# MAC15M, MAC15N

Preferred Device

## Triacs

### Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt — 250 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt — 9.0 A/ms minimum at 125°C
- Operational in Three Quadrants, Q1, Q2, and Q3
- Device Marking: Logo, Device Type, e.g., MAC15M, Date Code

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (-40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V <sub>DRM</sub> , V <sub>RRM</sub>	600 800	Volts
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 80°C)	I <sub>T(RMS)</sub>	15	A
Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>J</sub> = 125°C)	I <sub>TSM</sub>	150	A
Circuit Fusing Consideration (t = 8.3 ms)	I <sup>2</sup> t	93	A <sup>2</sup> s
Peak Gate Power (Pulse Width ≤ 1.0 μs, T <sub>C</sub> = 80°C)	P <sub>GM</sub>	20	Watts
Average Gate Power (t = 8.3 ms, T <sub>C</sub> = 80°C)	P <sub>G(AV)</sub>	0.5	Watts
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

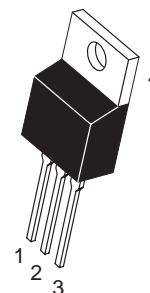
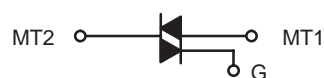
(1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



**ON Semiconductor**

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**TRIACS**  
**15 AMPERES RMS**  
**600 thru 800 VOLTS**



**TO-220AB**  
**CASE 221A**  
**STYLE 4**

#### PIN ASSIGNMENT

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

#### ORDERING INFORMATION

Device	Package	Shipping
MAC15M	TO220AB	50 Units/Rail
MAC15N	TO220AB	50 Units/Rail

**Preferred** devices are recommended choices for future use and best overall value.

# MAC15M, MAC15N

## THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Unit
$R_{\theta JC}$ $R_{\theta JA}$	Thermal Resistance — Junction to Case — Junction to Ambient	2.0 62.5	$^{\circ}C/W$
$T_L$	Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	260	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Symbol	Characteristic	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

$I_{DRM}$ , $I_{RRM}$	Peak Repetitive Blocking Current ( $V_D = \text{Rated } V_{DRM}, V_{RRM}$ ; Gate Open)	$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	— —	— —	0.01 2.0	mA
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## ON CHARACTERISTICS

$V_{TM}$	Peak On-State Voltage <sup>(1)</sup> ( $I_{TM} = \pm 21$ A Peak)	—	1.2	1.6	Volts
$I_{GT}$	Gate Trigger Current (Continuous DC) ( $V_D = 12$ V, $R_L = 100 \Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	5.0 5.0 5.0	13 16 18	35 35 35	mA
$I_H$	Hold Current ( $V_D = 12$ Vdc, Gate Open, Initiating Current = $\pm 150$ mA)	—	20	40	mA
$I_L$	Latching Current ( $V_D = 24$ V, $I_G = 35$ mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	— — —	33 36 33	50 80 50	mA
$V_{GT}$	Gate Trigger Voltage ( $V_D = 12$ V, $R_L = 100 \Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	0.5 0.5 0.5	0.75 0.72 0.82	1.5 1.5 1.5	Volts

## DYNAMIC CHARACTERISTICS

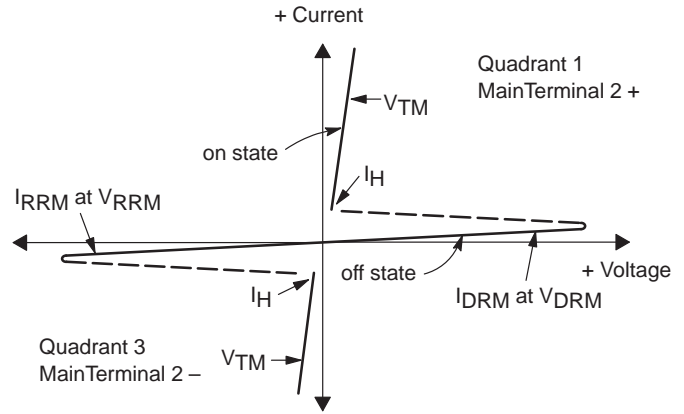
$(di/dt)_C$	Rate of Change of Commutating Current; See Figure 10. ( $V_D = 400$ V, $I_{TM} = 6.0$ A, Commutating $dv/dt = 24$ V/ $\mu$ s, Gate Open, $T_J = 125^{\circ}C$ , $f = 250$ Hz, No Snubber) $C_L = 10 \mu F$ $L_L = 40$ mH	9.0	—	—	A/ms
$dv/dt$	Critical Rate of Rise of Off-State Voltage ( $V_D = \text{Rated } V_{DRM}$ , Exponential Waveform, Gate Open, $T_J = 125^{\circ}C$ )	250	—	—	V/ $\mu$ s

(1) Pulse Test: Pulse Width  $\leq 2.0$  ms, Duty Cycle  $\leq 2\%$ .

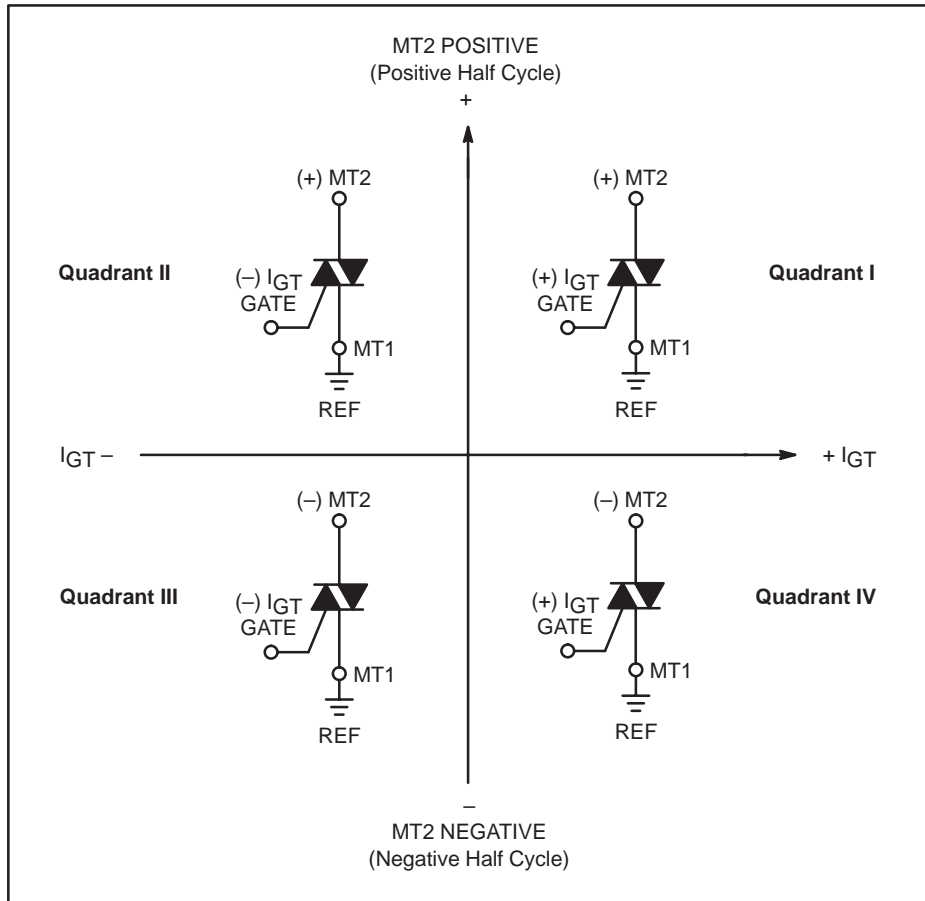
# MAC15M, MAC15N

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
$I_H$	Holding Current



### Quadrant Definitions for a Triac



All polarities are referenced to MT1.  
 With in-phase signals (using standard AC lines) quadrants I and III are used.

# MAC15M, MAC15N

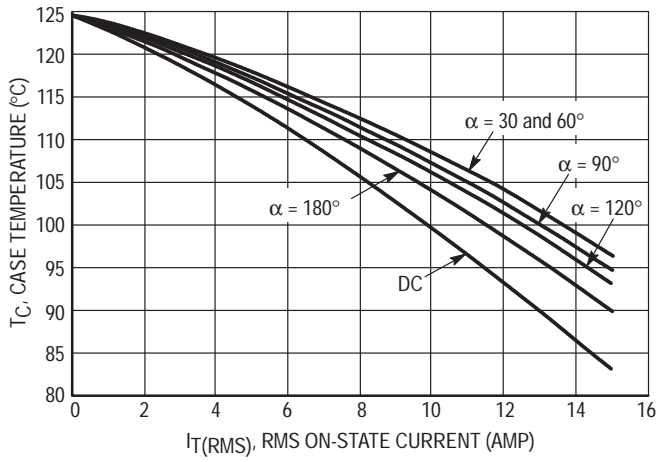


Figure 1. RMS Current Derating

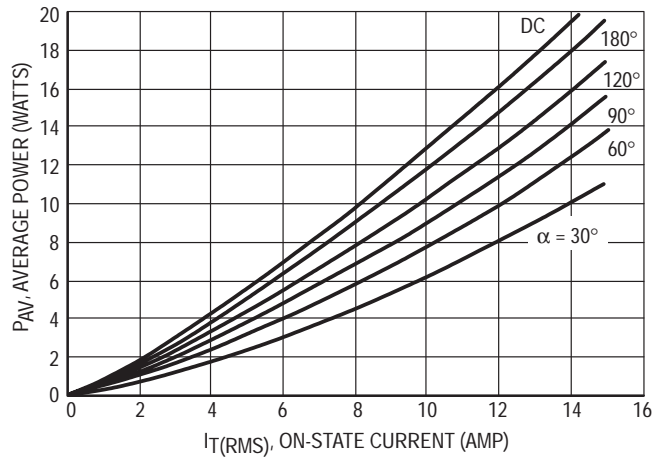


Figure 2. On-State Power Dissipation

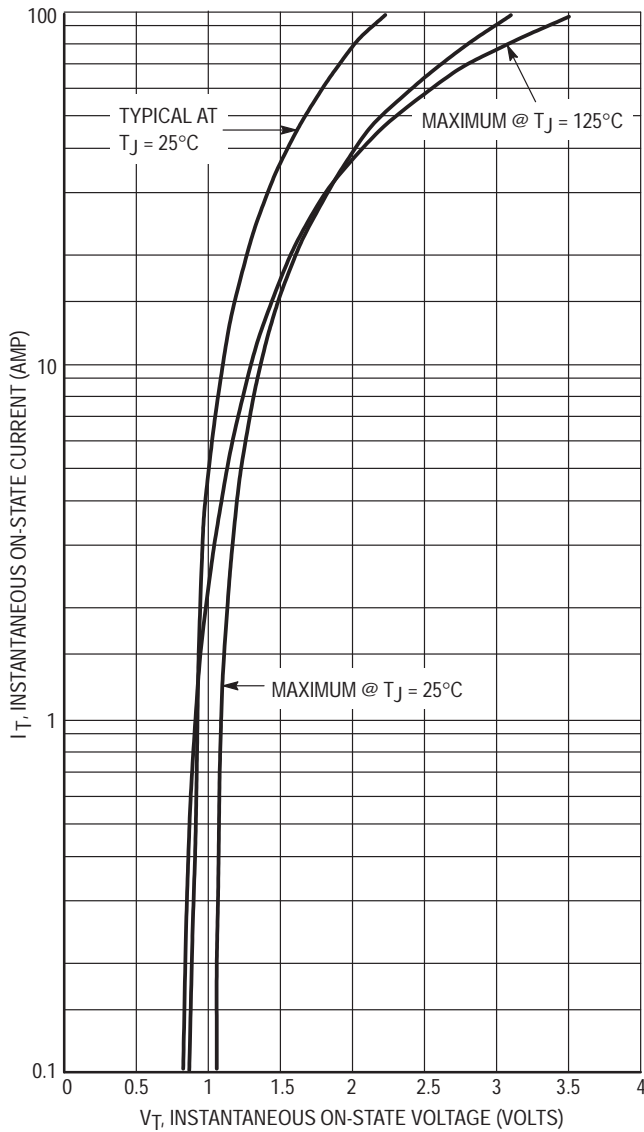


Figure 3. On-State Characteristics

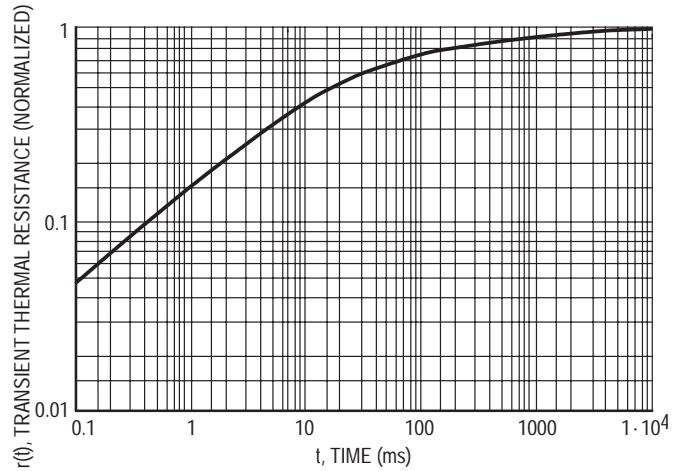


Figure 4. Transient Thermal Response

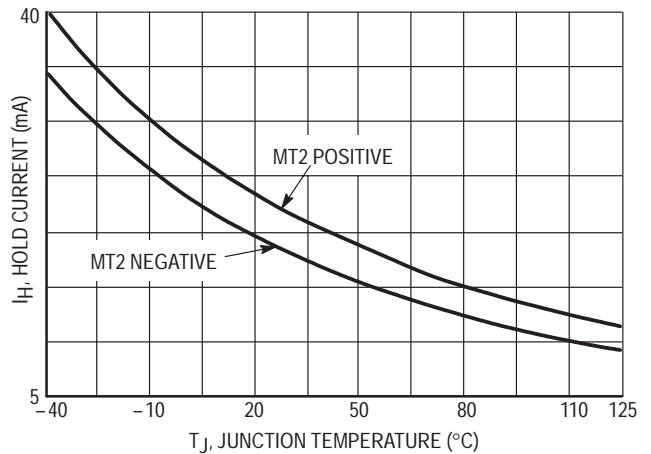
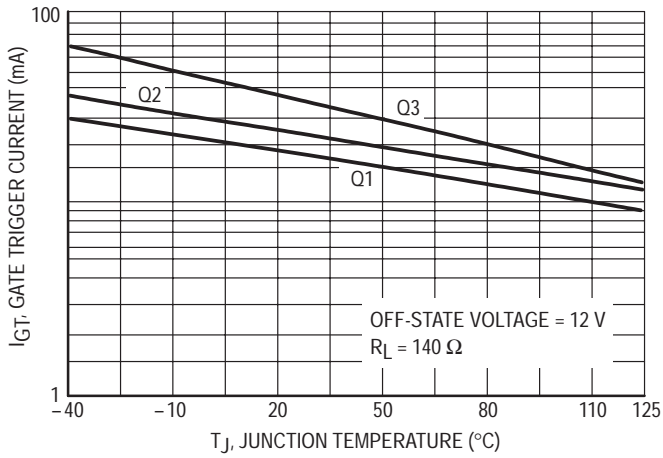
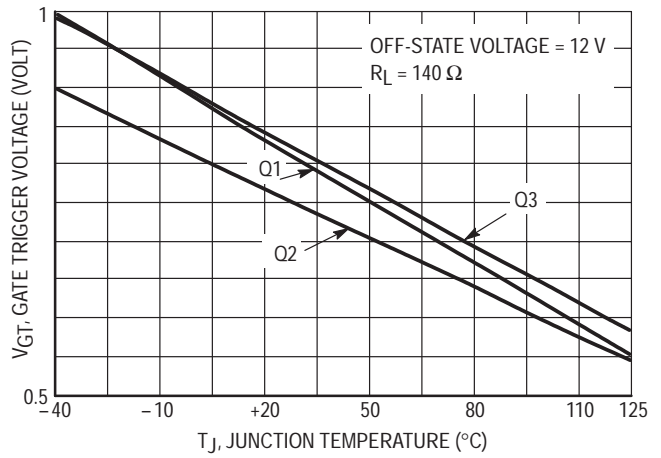


Figure 5. Hold Current Variation

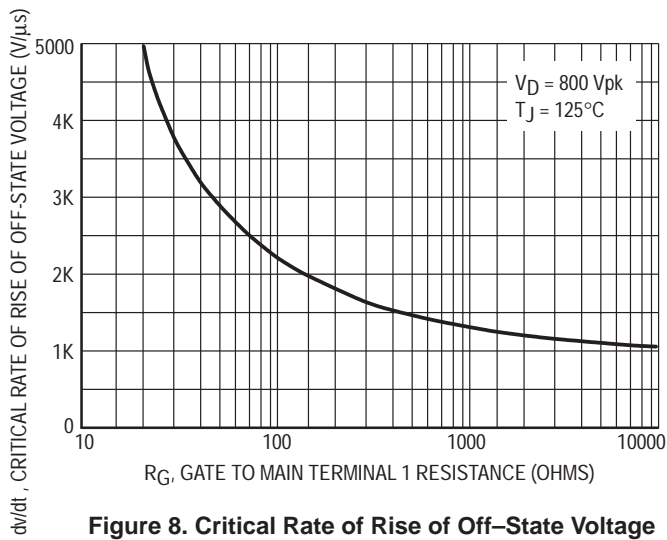
# MAC15M, MAC15N



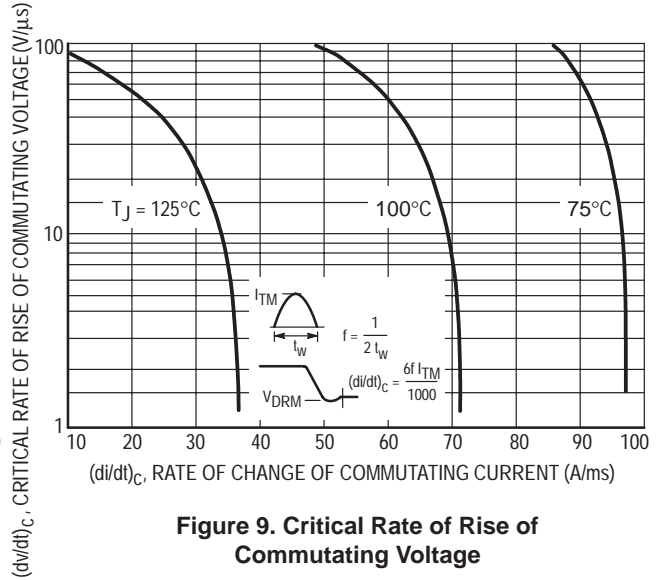
**Figure 6. Typical Holding Current versus Junction Temperature**



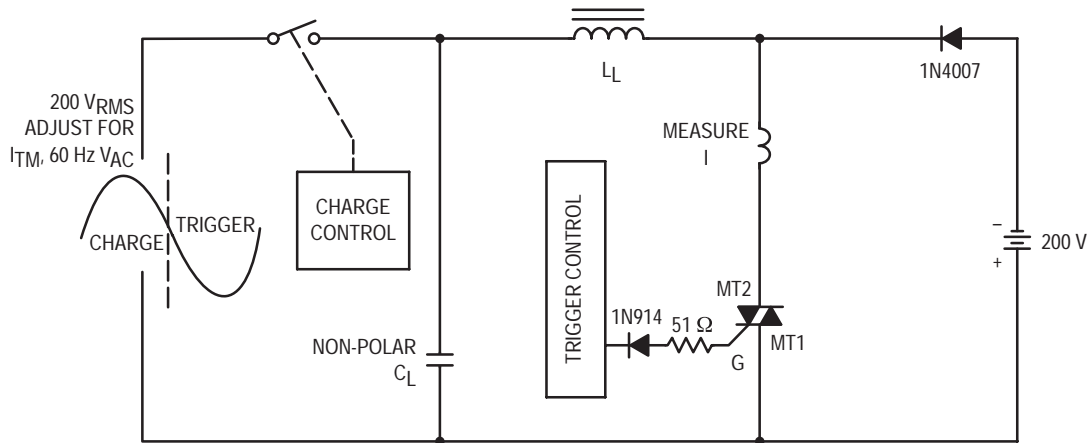
**Figure 7. Gate Trigger Voltage versus Junction Temperature**



**Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential)**



**Figure 9. Critical Rate of Rise of Commutating Voltage**



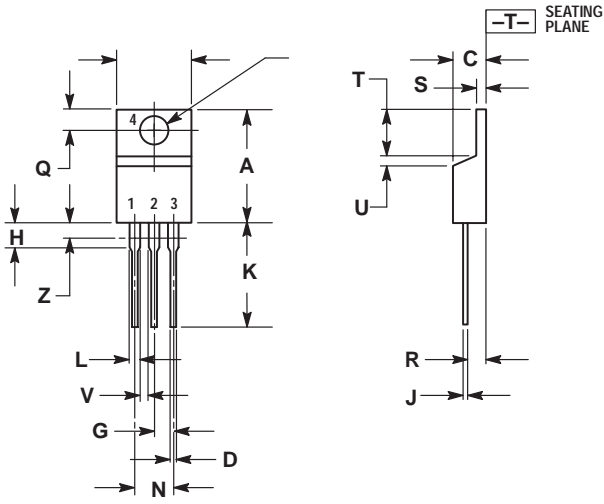
Note: Component values are for verification of rated  $(di/dt)_C$ . See AN1048 for additional information.

**Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current  $(di/dt)_C$**

# MAC15M, MAC15N

## PACKAGE DIMENSIONS

TO-220AB  
CASE 221A-09  
ISSUE Z




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

**Notes**

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